**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOT429 (3-lead TO247) plastic package.

## 2. Features and benefits

- Low leakage current
- Low thermal resistance
- · Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_R$	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	30	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse	-	-	60	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	270	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	300	Α
Static charac	teristics					,
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
Dynamic cha	racteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	18	22	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ $\mu s; T_i = 25 ^{\circ}C; Fig. 7$	-	29	-	ns

# 5. Pinning information

## **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		K ——— A
2	K	cathode		001aaa020
3	Α	anode		
mb	mb	mounting base; connected to cathode		
			TO-247 (SOT429)	

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYC30WT-600P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429		

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; $T_{mb}$ ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	30	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse	-	60	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	270	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	300	Α
T <sub>stg</sub>	storage temperature		-65	175	°C
T <sub>j</sub>	junction temperature		-	175	°C

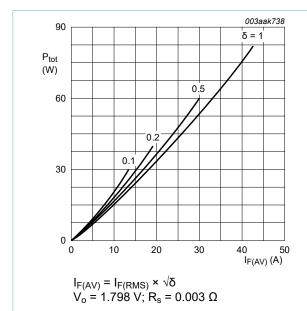
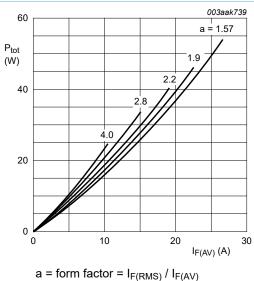


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $V_0 = 1.798V; R_s = 0.003 \Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

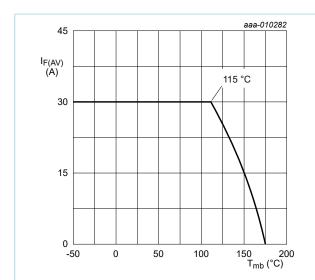


Fig. 3. Forward current as a function of mounting base temperature; maximum values

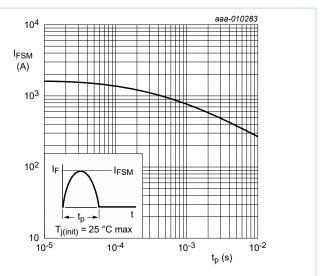
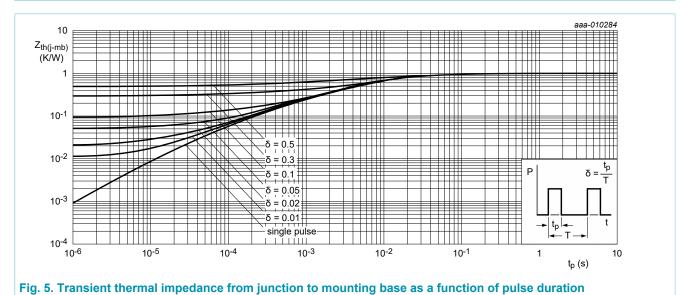


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

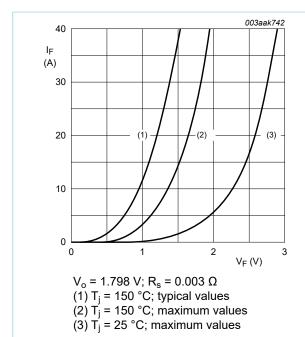


BYC30WT-600P

# 9. Characteristics

## **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
$V_{F}$	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	1	mA
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	18	22	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	70	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	29	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	3.5	-	Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	7.6	-	Α
Q <sub>r</sub>	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	50	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_i = 125 ^{\circ}\text{C}; Fig. 7$	-	280	-	nC



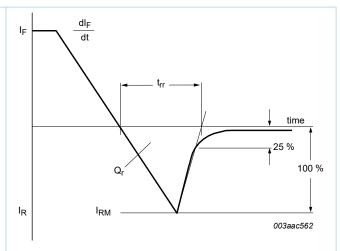
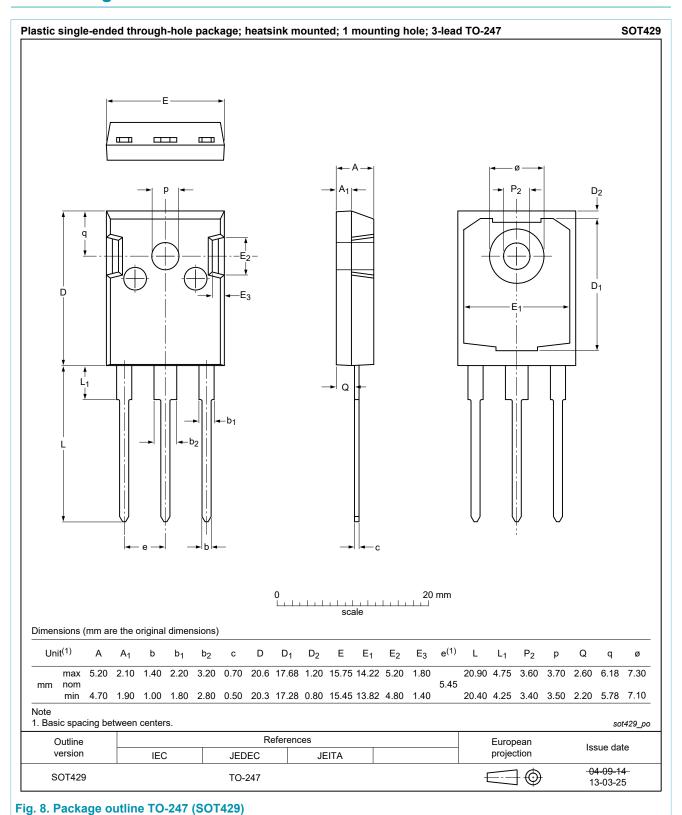


Fig. 7. Reverse recovery definitions; ramp recovery

Fig. 6. Forward current as a function of forward voltage

# 10. Package outline



# 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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